

Schottky Barrier Diode

DESCRIPTION

Silicon Epitaxial Planar

FEATURE

- Small surface mounting type
- High reliability

APPLICATION

High speed switching for detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note Book PC, etc.)



CASE: DFN1006- 2



MARKING: F



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Non-repetitive Peak forward surge current @ t=8.3ms	I_{FSM}	1	A
Power dissipation	P_D	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1000	°C/W
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+150	°C

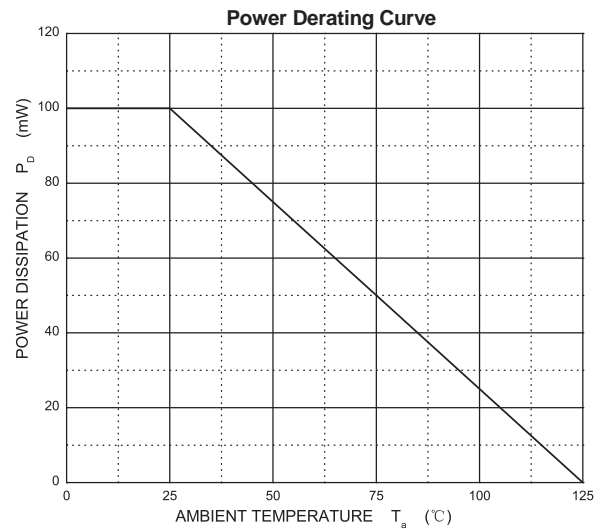
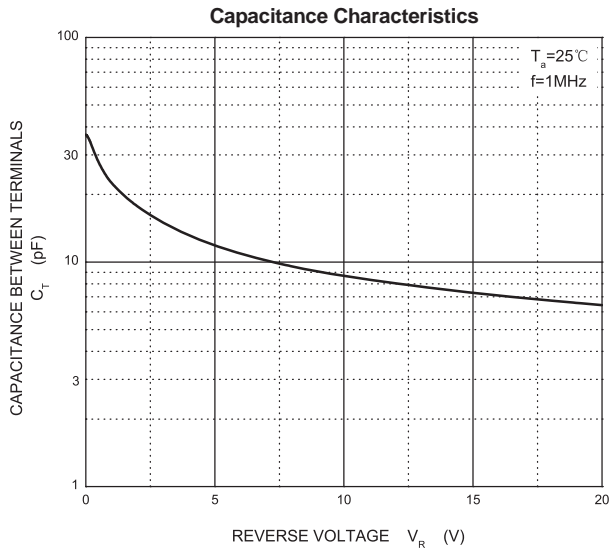
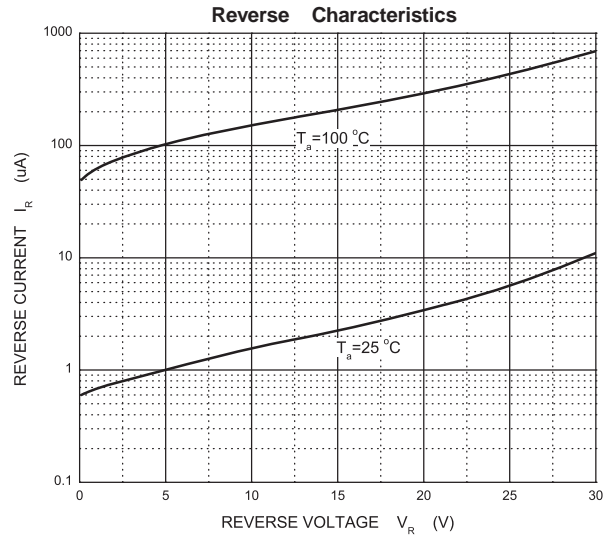
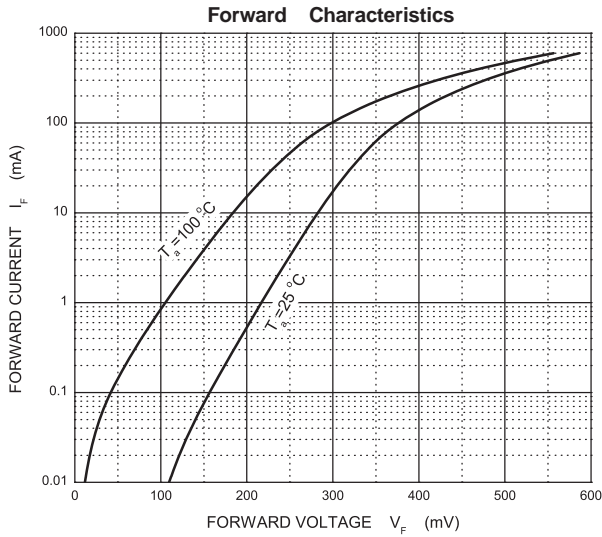
Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_{F1}			0.35	V	$I_F=10mA$
	V_{F2}			0.5	V	$I_F=200mA$
Reverse current	I_R			10	μA	$V_R=10V$

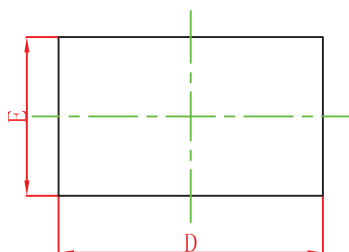


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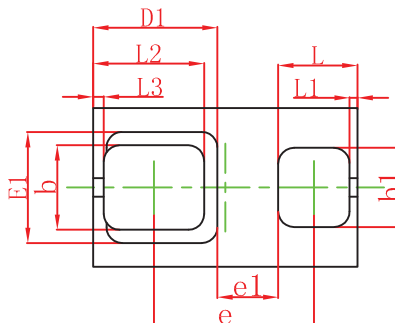
Electrical characteristic curves ($T_A=25^\circ\text{C}$ unless otherwise specified)



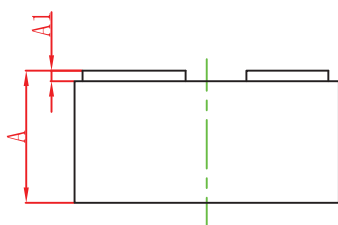
DFN-1006 Package Outline Dimensions



TOP VIEW



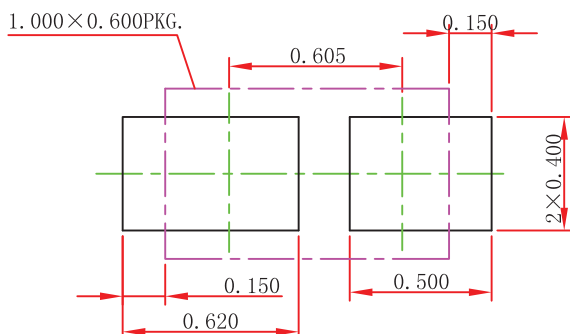
BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.100	0.000	0.004
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.470REF.		0.019REF.	
E1	0.420REF.		0.017REF.	
b	0.270	0.370	0.011	0.015
b1	0.250	0.350	0.010	0.014
e	0.555	0.655	0.022	0.026
e1	0.230REF.		0.009REF.	
L	0.250	0.350	0.010	0.014
L1	0.030REF.		0.001REF.	
L2	0.370	0.470	0.015	0.019
L3	0.040REF.		0.002REF.	

DFN-1006 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.